# Heidemarie Schmidt

List of Publications by Year
in descending order



| 37 | 1,161 | 471509 17 | 377865 34 |
|---|---|---|---|
| papers | citations | h-index | g-index |

| 38 | 38 | 38 | 1829 |
|---|---|---|---|
| all docs | docs citations | times ranked | citing authors |

| # | Article | IF | Citations |
|---|---|---|---|
| 1 | Analysis of Low-Temperature Magnetotransport Properties of NbN Thin Films Grown by Atomic Layer Deposition. Magnetochemistry, 2022, 8, 33. | 2.4 | 0 |
| 2 | Prospects for application of ferroelectric manganites with controlled vortex density. Applied Physics Letters, 2021, 118, . | 3.3 | 3 |
| 3 | Electrochemical growth mechanism of nanoporous platinum layers. Communications Chemistry, 2021, 4, . | 4.5 | 2 |
| 4 | Wafer-level uniformity of atomic-layer-deposited niobium nitride thin films for quantum devices. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, 052401. | 2.1 | 11 |
| 5 | Increased static dielectric constant in ZnMnO and ZnCoO thin films with bound magnetic polarons. Scientific Reports, 2020, 10, 6698. | 3.3 | 17 |
| 6 | Charged domains in ferroelectric, polycrystalline yttrium manganite thin films resolved with scanning electron microscopy. Nanotechnology, 2020, 31, 31LT01. | 2.6 | 4 |
| 7 | Electroforming-free resistive switching in yttrium manganite thin films by cationic substitution. Journal of Applied Physics, 2019, 126, . | 2.5 | 9 |
| 8 | Tunable large field magnetoconductance of ZnO, ZnMnO, and ZnCoO thin films. Journal of Applied Physics, 2019, 125, 215305. | 2.5 | 3 |
| 9 | Field-Driven Hopping Transport of Oxygen Vacancies in Memristive Oxide Switches with Interface-Mediated Resistive Switching. Physical Review Applied, 2018, 10, . | 3.8 | 34 |
| 10 | Electroforming-free resistive switching in polycrystalline YMnO3 thin films. Journal of Applied Physics, 2018, 124, . | 2.5 | 5 |
| 11 | Thouless length and valley degeneracy factor of ZnMnO thin films with anisotropic, highly conductive surface layers. Journal of Applied Physics, 2017, 121, . | 2.5 | 2 |
| 12 | An Energyâ€Efficient, BiFeO<sub>3</sub>â€Coated Capacitive Switch with Integrated Memory and Demodulation Functions. Advanced Electronic Materials, 2016, 2, 1500352. | 5.1 | 19 |
| 13 | Bipolar resistive switching in YMnO3/Nb:SrTiO3pn-heterojunctions. Nanotechnology, 2016, 27, 455201. | 2.6 | 20 |
| 14 | Plasticity in memristive devices for spiking neural networks. Frontiers in Neuroscience, 2015, 9, 51. | 2.8 | 188 |
| 15 | Single pairing spike-timing dependent plasticity in BiFeO3 memristors with a time window of 25 ms to 125 Î¼s. Frontiers in Neuroscience, 2015, 9, 227. | 2.8 | 54 |
| 16 | Novel implementation of memristive systems for data encryption and obfuscation. Journal of Applied Physics, 2014, 115, . | 2.5 | 11 |
| 17 | Bipolar Electric-Field Enhanced Trapping and Detrapping of Mobile Donors in BiFeO<sub>3</sub> Memristors. ACS Applied Materials & Interfaces, 2014, 6, 19758-19765. | 8.0 | 84 |
| 18 | Exploiting Memristive BiFeO<sub>3</sub> Bilayer Structures for Compact Sequential Logics. Advanced Functional Materials, 2014, 24, 3357-3365. | 14.9 | 116 |

| # | Article | IF | Citations |
|---|---|---|---|
| 19 | Transport in ZnCoO thin films with stable bound magnetic polarons. APL Materials, 2014, 2, . | 5.1 | 6 |
| 20 | Key concepts behind forming-free resistive switching incorporated with rectifying transport properties. Scientific Reports, 2013, 3, 2208. | 3.3 | 48 |
| 21 | Improved retention of nonvolatile bipolar BiFeO<sub>3</sub> resistive memories validated by memristance measurements. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 636-639. | 0.8 | 16 |
| 22 | Substrate effect on the resistive switching in BiFeO3 thin films. Journal of Applied Physics, 2012, 111, . | 2.5 | 26 |
| 23 | Hysteretic anomalous Hall effect in a ferromagnetic, Mn-rich Ge:Mn nanonet. Applied Physics Letters, 2012, 100, . | 3.3 | 13 |
| 24 | Transition metal diffusion in diluted magnetic Si and GaAs prepared by pulsed laser processing. Journal of Applied Physics, 2012, 111, . | 2.5 | 5 |
| 25 | Decisive role of oxygen vacancy in ferroelectric versus ferromagnetic Mn-doped BaTiO3 thin films. Journal of Applied Physics, 2011, 109, . | 2.5 | 112 |
| 26 | Nonvolatile bipolar resistive switching in Au/BiFeO3/Pt. Journal of Applied Physics, 2011, 109, 124117. | 2.5 | 116 |
| 27 | Effect of the substrate on the insulatorâ€“metal transition of vanadium dioxide films. Journal of Applied Physics, 2011, 109, . | 2.5 | 43 |
| 28 | Role of Coulomb blockade and spin-flip scattering in tunneling magnetoresistance of FeCo-Si-O nanogranular films. Journal of Applied Physics, 2011, 109, . | 2.5 | 14 |
| 29 | Reduced leakage current in BiFeO3 thin films with rectifying contacts. Applied Physics Letters, 2011, 98, . | 3.3 | 39 |
| 30 | Voigt effect measurement on PLD grown NiO thin films. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 334-337. | 0.8 | 3 |
| 31 | Application of pulsed laser annealing to ferromagnetic GaMnAs. Physical Review B, 2010, 81, . | 3.2 | 27 |
| 32 | The importance of hole concentration in establishing carrier-mediated ferromagnetism in Mn doped Ge. Applied Physics Letters, 2010, 96, . | 3.3 | 16 |
| 33 | Microstructure, electrical, magnetic, and extraordinary Hall effect studies in Ni:SiO2 nanogranular films synthesized by atom beam sputtering. Journal of Applied Physics, 2010, 107, . | 2.5 | 8 |
| 34 | Mn-doped Ge and Si: A Review of the Experimental Status. Materials, 2010, 3, 5054-5082. | 2.9 | 32 |
| 35 | Hysteresis in the magnetotransport of manganese-doped germanium: Evidence for carrier-mediated ferromagnetism. Physical Review B, 2010, 81, . | 3.2 | 23 |
| 36 | Memory effect of Mn5Ge3 nanomagnets embedded inside a Mn-diluted Ge matrix. Applied Physics Letters, 2009, 95, . | 3.3 | 14 |

| # | Article | IF | Citations |
|---|---|---|---|
| 37 | Anomalous Hall resistance in Ge:Mn systems with low Mn concentrations. Applied Physics Letters, 2009, 95, . | 3.3 | 18 |